

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max $T_C = +25^\circ C$
60V	6m Ω @ $V_{GS} = 10V$	80A
	8.5m Ω @ $V_{GS} = 4.5V$	70A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

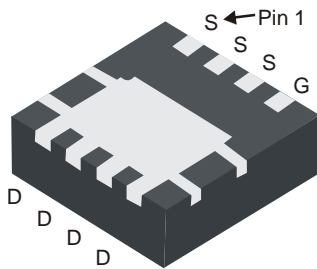
- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

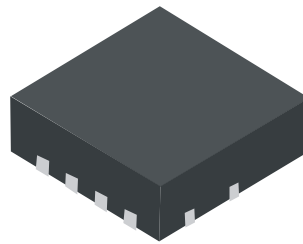
- Low $R_{DS(ON)}$ – Ensures On-State Losses are Minimized
- Excellent $Q_{gd} \times R_{DS(ON)}$ Product (FOM)
- Advanced Technology for DC-DC Converters
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area by enabling smaller end products
- 100% UIS (Avalanche) Rated
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

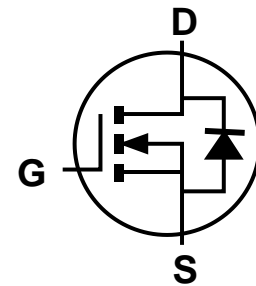
- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)

 POWERDI[®]3333-8


Bottom View



Top View



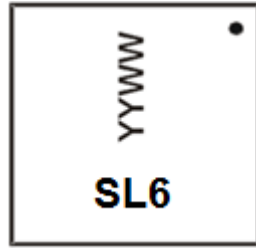
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6007LFG-7	POWERDI [®] 3333-8	2,000/Tape & Reel
DMT6007LFG-13	POWERDI [®] 3333-8	3,000/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information

 POWERDI[®]3333-8


SL6 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Digit of Year (ex: 14 = 2014)
 WW = Week Code (01 ~ 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (Note 5) $V_{GS} = 10\text{V}$	I_D	$T_A = +25^\circ\text{C}$	15
		$T_A = +70^\circ\text{C}$	12
	I_D	$T_C = +25^\circ\text{C}$	80
		$T_C = +70^\circ\text{C}$	65
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	80	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)	I_{DM}	80	A
Avalanche Current, L=0.1mH	I_{AS}	20	A
Avalanche Energy, L=0.1mH	E_{AS}	20	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	2.2	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	55	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)	P_D	62.5	W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	2	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 5. $R_{\theta JA}$ is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.
 6. Short duration pulse test used to minimize self-heating effect.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(TH)}	0.8	—	2	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	4.5	6	mΩ	V _{GS} = 10V, I _D = 20A
		—	6.5	8.5		V _{GS} = 4.5V, I _D = 15A
Forward Transconductance	G _{FS}	—	100	—	S	V _{DS} = 5V, I _D = 20A
Diode Forward Voltage	V _{SD}	—	0.9	1.2	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	—	2090	—	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	746	—		
Reverse Transfer Capacitance	C _{rss}	—	38.5	—		
Gate Resistance	R _g	—	0.59	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	19.3	—	nC	V _{DS} = 30V, I _D = 20A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	41.3	—		
Gate-Source Charge	Q _{gs}	—	6.0	—		
Gate-Drain Charge	Q _{gd}	—	8.8	—		
Turn-On Delay Time	t _{D(ON)}	—	5.7	—	ns	V _{DD} = 30V, V _{GS} = 10V, I _D = 20A, R _G = 3Ω
Turn-On Rise Time	t _R	—	4.3	—		
Turn-Off Delay Time	t _{D(OFF)}	—	23.4	—		
Turn-Off Fall Time	t _F	—	9.7	—		
Body Diode Reverse Recovery Time	t _{RR}	—	35.4	—	ns	I _F = 20A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	—	38.2	—	nC	

Note: 7. Guaranteed by design. Not subject to product testing.

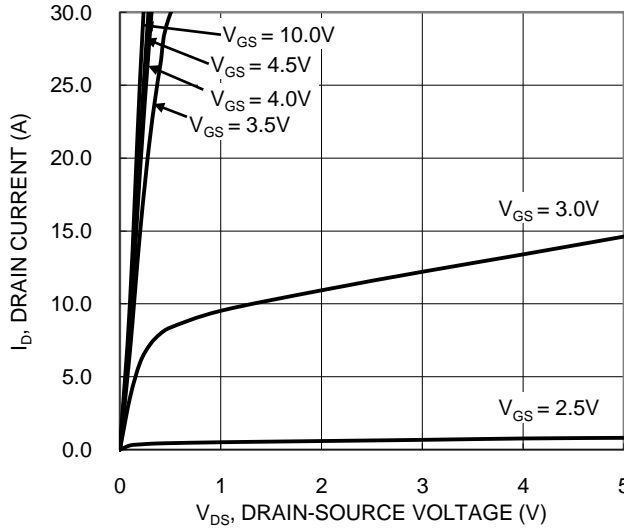


Figure 1. Typical Output Characteristic

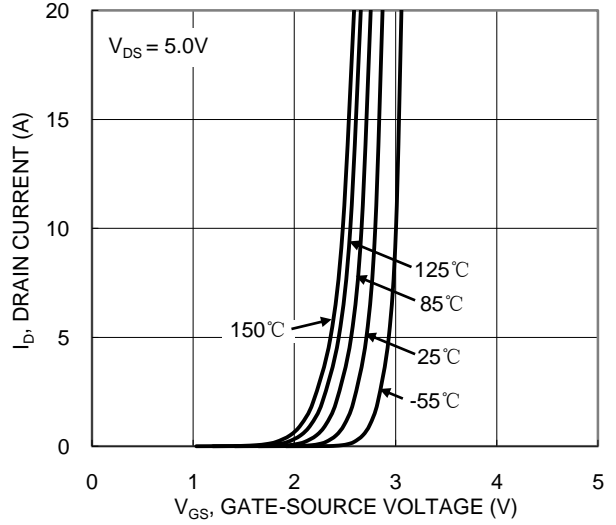


Figure 2. Typical Transfer Characteristic

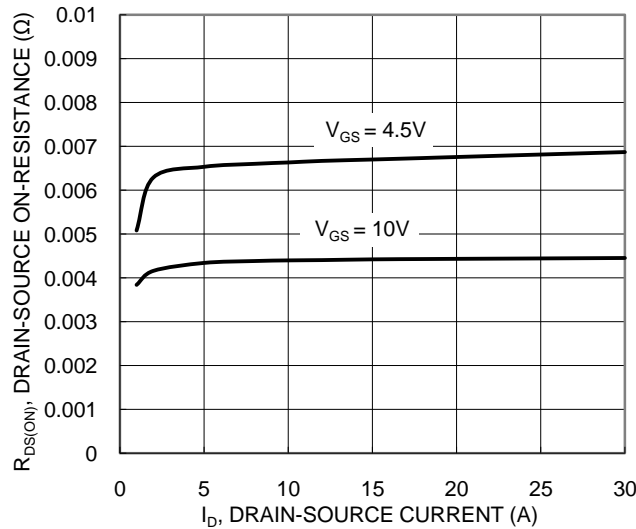


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

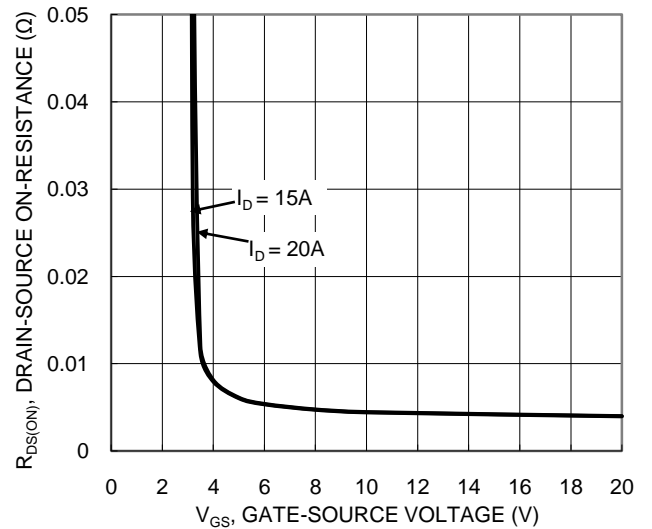


Figure 4. Typical Transfer Characteristic

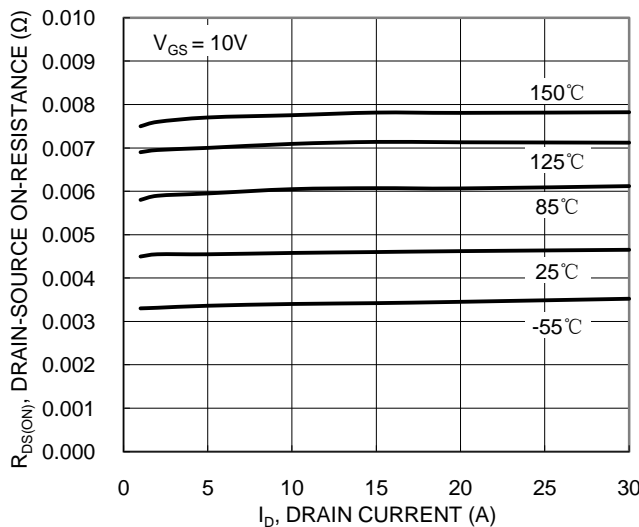


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

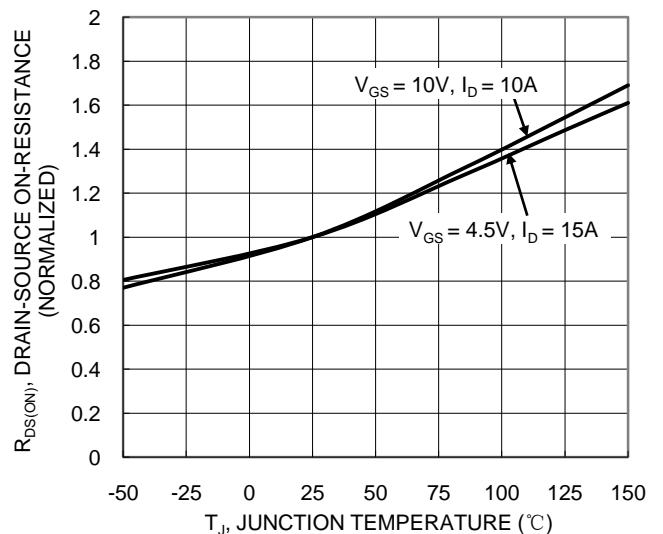


Figure 6. On-Resistance Variation with Temperature

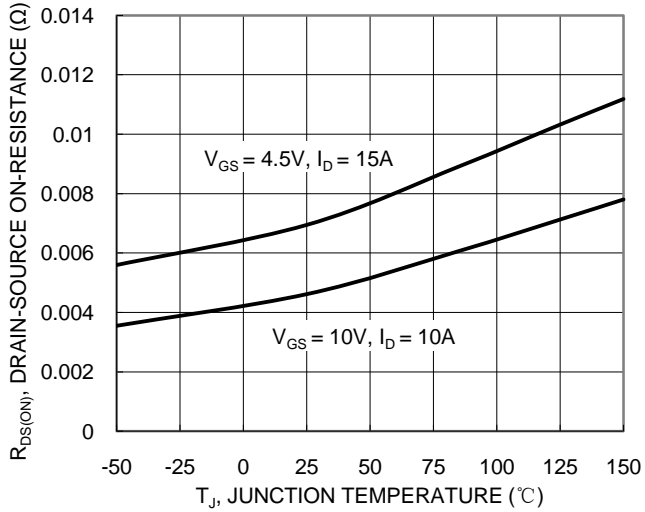


Figure 7. On-Resistance Variation with Temperature

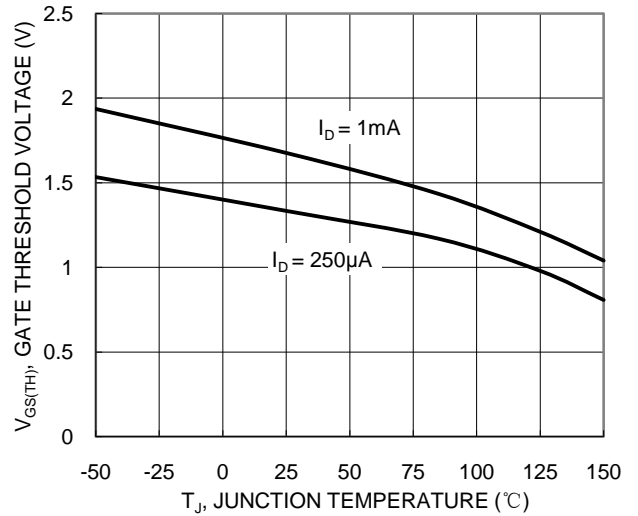


Figure 8. Gate Threshold Variation vs. Junction Temperature

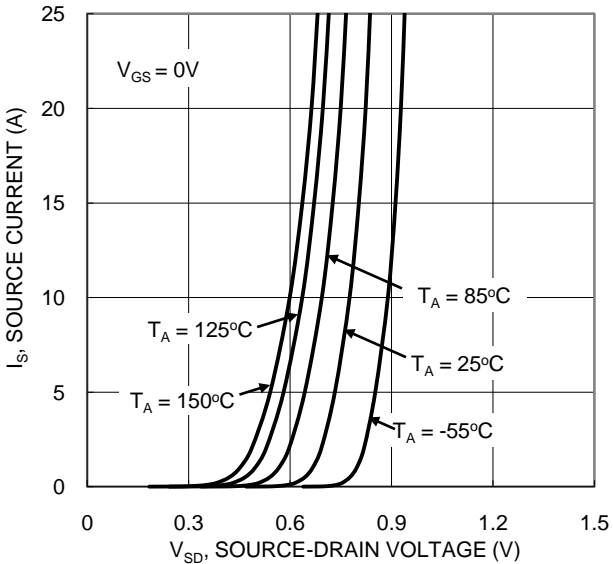


Figure 9. Diode Forward Voltage vs. Current

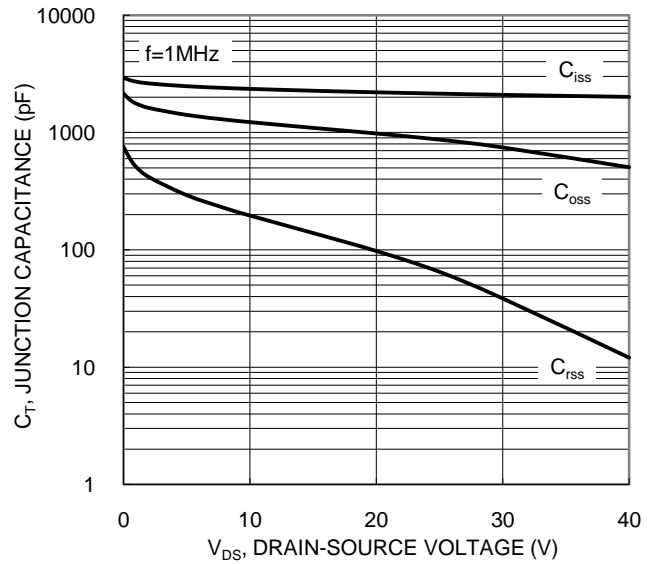


Figure 10. Typical Junction Capacitance

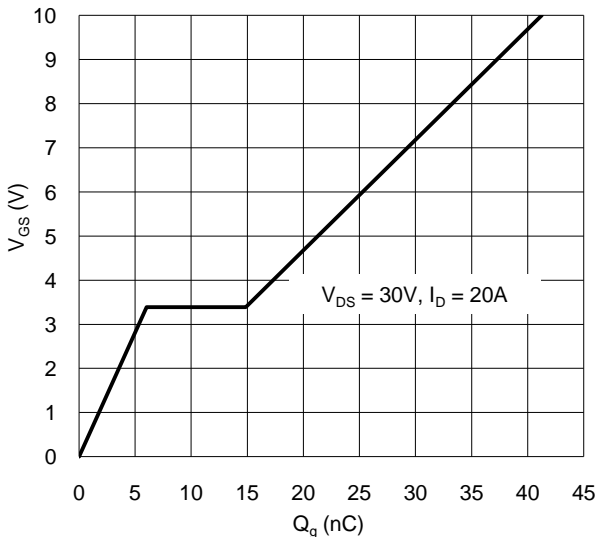


Figure 11. Gate Charge

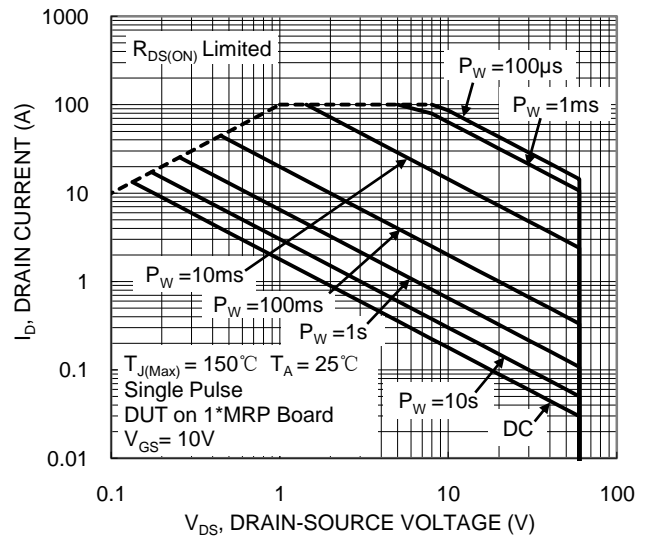


Figure 12. SOA, Safe Operation Area

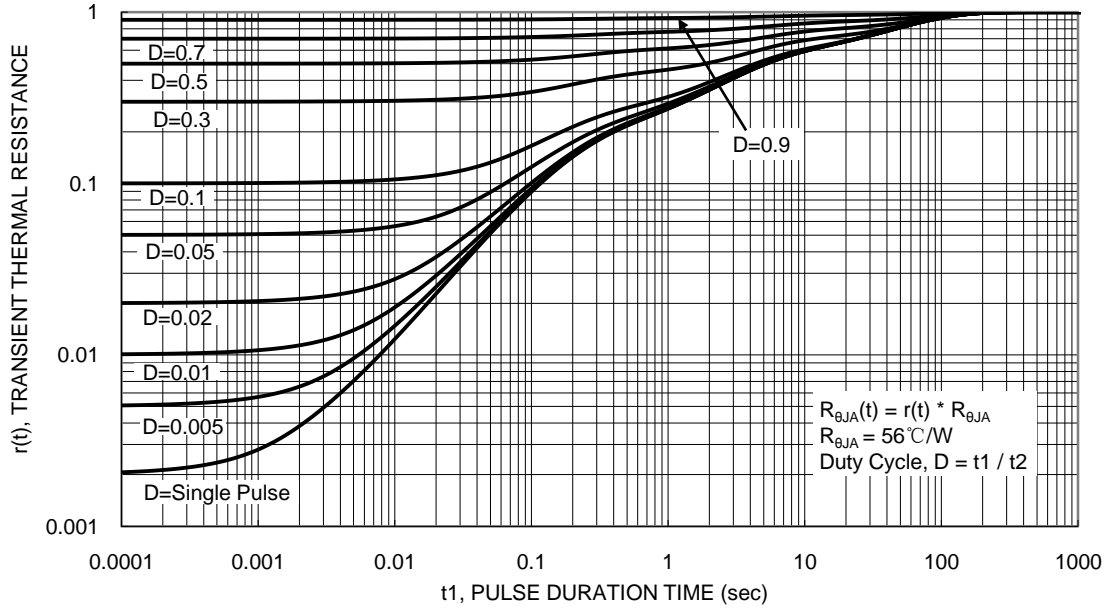
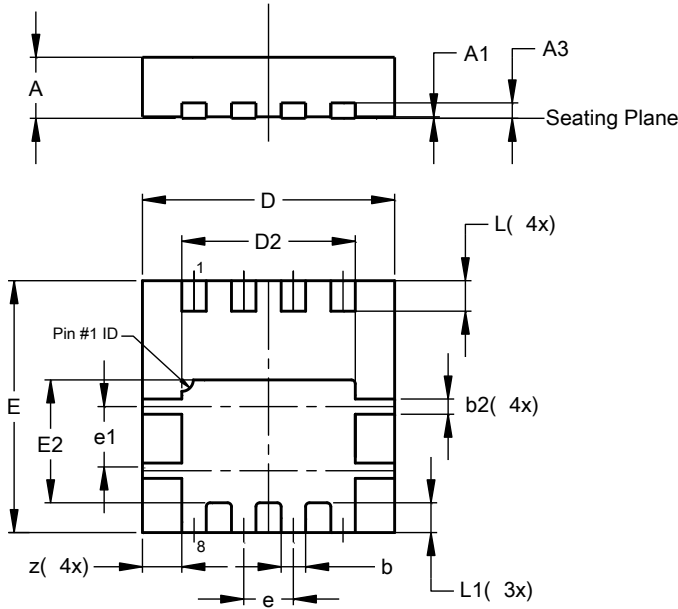


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

POWERDI®3333-8



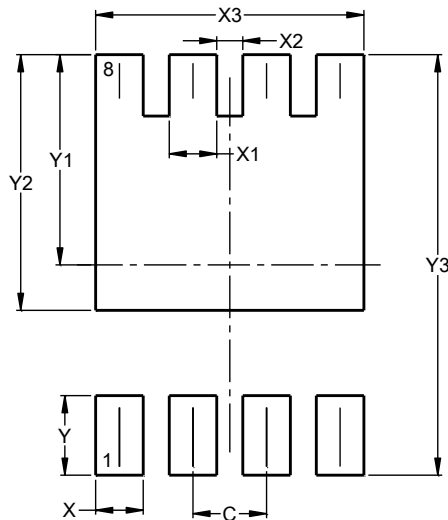
POWERDI®3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	-	-	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
e	-	-	0.65
e1	0.79	0.89	0.84
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

NEW PRODUCT

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

POWERDI®3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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